

BCW29,30

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)

GENERAL PURPOSE TRANSISTOR

PNP SILICON

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	20	Vdc
Collector-Base Voltage	V_{CBO}	30	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Collector Current — Continuous	I_C	100	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
*Total Device Dissipation, $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	350 2.8	mW mW/ $^\circ\text{C}$
Storage Temperature	T_{stg}	150	$^\circ\text{C}$
*Thermal Resistance Junction to Ambient	R_{\thetaJA}	357	$^\circ\text{C/W}$

*Package mounted on 99.5% alumina 10 x 8 x 0.6 mm.

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage ($I_C = 2.0 \text{ mAdc}, I_E = 0$)	$V_{(BR)CEO}$	20	—	Vdc
Collector-Emitter Breakdown Voltage ($I_C = 100 \mu\text{Adc}, V_{EB} = 0$)	$V_{(BR)CES}$	30	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 10 \mu\text{Adc}, I_C = 0$)	$V_{(BR)CBO}$	30	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10 \mu\text{Adc}, I_C = 0$)	$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 20 \text{ Vdc}, I_E = 0$) ($V_{CB} = 20 \text{ Vdc}, I_E = 0, T_A = 100^\circ\text{C}$)	I_{CBO}	— —	100 10	nAdc μAdc
ON CHARACTERISTICS				
DC Current Gain ($I_C = 2.0 \text{ mAdc}, V_{CE} = 5.0 \text{ Vdc}$)	h_{FE} BCW29 BCW30	120 215	260 500	—
Collector-Emitter Saturation Voltage ($I_C = 10 \text{ mAdc}, I_B = 0.5 \text{ mAdc}$)	$V_{CE(\text{sat})}$	—	0.3	Vdc
Base-Emitter On Voltage ($I_C = 2.0 \text{ mAdc}, V_{CE} = 5.0 \text{ Vdc}$)	$V_{BE(\text{on})}$	0.6	0.75	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Output Capacitance ($I_E = 0, V_{CE} = 10 \text{ Vdc}, f = 1.0 \text{ MHz}$)	C_{obo}	—	7.0	pF
Noise Figure ($I_C = 0.2 \text{ mAdc}, V_{CE} = 5.0 \text{ Vdc}, R_S = 2.0 \text{ k}\Omega, f = 1.0 \text{ kHz},$ $BW = 200 \text{ Hz}$)	NF	—	10	dB